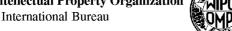
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(54) Title: PROCESS OF PREPARING REGIOREGULAR POLYMERS

(57) Abstract: The invention relates to a process of preparing regionegular polymers, in particular head-to-tail (HT) poly-(3-substituted) thiophenes with high regioregularity, to novel polymers prepared by this process, and to the use of the novel polymers as semiconductors or charge transport materials in optical, electrooptical or electronic devices including field effect transistors (FETs), electroluminescent, photovoltaic and sensor devices, to FETs and other semiconducting components or materials comprising the novel polymers.



WO 2006/084545

PCT/EP2006/000360

-1-

Process of Preparing Regioregular Polymers

Field of Invention

The invention relates to a process of preparing regioregular polymers, in particular head-to-tail (HT) poly-(3-substituted) thiophenes with high regioregularity, and to novel polymers prepared by this process. The invention further relates to the use of the novel polymers as semiconductors or charge transport materials in optical, electrooptical or electronic devices including field effect transistors (FETs), electroluminescent, photovoltaic and sensor devices. The invention further relates to FETs and other semiconducting components or materials comprising the novel polymers.

15 Background and Prior Art

Organic materials have recently shown promise as the active layer in organic based thin film transistors and organic field effect transistors (OFETs) [see H. E. Katz, Z. Bao and S. L. Gilat, *Acc. Chem. Res.*, 2001, **34**, 5, 359]. Such devices have potential applications in smart cards, security tags and the switching element in flat panel displays. Organic materials are envisaged to have substantial cost advantages over their silicon analogues if they can be deposited from solution, as this enables a fast, large-area fabrication route.

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The performance of the device is principally based upon the charge carrier mobility of the semiconducting material and the current on/off ratio, so the ideal semiconductor should have a low conductivity in the off state, combined with a high charge carrier mobility (> 1 x 10⁻³ cm² V⁻¹ s⁻¹). In addition, it is important that the semiconducting material is relatively stable to oxidation i.e. it has a high ionisation potential, as oxidation leads to reduced device performance.

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In prior art regioregular head-to-tail (HT) poly-(3-alkylthiophene), in particular poly-(3-hexylthiophene), has been suggested for use as semiconducting material, as it shows charge carrier mobility between

 1×10^{-5} and $0.1 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$. Also, poly-(3-alkylthiophene) shows good solubility in organic solvents and is solution processable to fabricate large area films.

- A high regioregularity of the poly-(3-alkylthiophene) is important for its electronic and photonic properties, as it leads to improved packing and optimised microstructure, leading to improved charge carrier mobility [see US 6,166,172, H. Sirringhaus et al., *Science*, 1998, 280, 1741-1744; H. Sirringhaus et al., *Nature*, 1999, 401, 685-688; and H. Sirringhaus, et al., *Synthetic Metals*, 2000, 111-112, 129-132]. The regioregularity is strongly influenced by the method of preparing the polymer.
- Several methods to produce highly regioregular HT-poly-(3-alkylthiophene) have been reported in prior art, for example in the review of R.D. McCullough, *Adv. Mater.*,1998, **10(2)**, 93-116 and the references cited therein.
- Known methods to prepare HT-poly(3-alkylthiophene) with a regioregularity ≥ 90 % starting from 2,5,dibromo-3-alkylthiophene include for example the "Rieke method", by reacting the educt (wherein R is alkyl) with highly reactive zinc in THF as illustrated below.

Also known is the method described in McCullough et al., *Adv. Mater.*,1999, **11(3)**, 250-253 and in EP 1 028 136 and US 6,166,172, the entire disclosure of these documents being incorporated into this application by reference. According to this route the educt is reacted with methylmagnesium bromide in THF as shown below.

It was also reported to prepare regionegular poly(3-alkylthiophene) by the "Stille-method" (see Stille, Iraqi, Barker et al., *J. Mater. Chem.*, 1998, **8**, 25) as illustrated below

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or by the "Suzuki-method" (see Suzuki, Guillerez, Bidan et al., *Synth. Met.*, 1998, **93**, 123) as shown below.

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$$(OR)_2B$$
 S
 R
 $Pd(PPh_3)_4$
 $*$
 S
 n
 $*$

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However, the methods described in prior art have several drawbacks. Thus, for example the Rieke method requires the costly and difficult preparation of the highly active "Rieke zinc". The Stille and Suzuki methods require an extra processing step which reduces the process efficiency. The McCullough method requires the costly Grignard reagent methylmagnesium bromide. Additionally, it produces methyl bromide as a by-product in stoichiometrical quantities which especially in large scale production causes environmental problems. As methyl bromide cannot be eliminated from the exhaust gases with a gas washer, costly techniques and means for exhaust air combustion are needed.

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Prior art also reports the preparation of unsubstituted polythiophene by Nickel-catalysed coupling of a Grignard reagent that is formed from the reaction of a 2,5-dihalogenated thiophene with magnesium.

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This route was first reported in 1984 (J. P. Montheard; T. Pascal, *Synth. Met*, 1984, **9**, 389 and M. Kobayashi; J. Chen; T.-C. Chung; F. Moraes; A. J. Heeger; F. Wudl, *Synth. Met*, 1984, **9**, 77). However, this method yielded only low molecular weights. Also these polymers only have low solubility, compared to 3-alkyl substituted polythiophenes.

There are also reports on the preparation of poly (3-alkyl thiophene) using the Nickel-catalysed coupling of a Grignard reagent formed from 2,5-dihalogenated 3-alkylthiophene with magnesium as illustrated below.

T. Yamamoto, K.-I. Sanechika, A. Yamamoto, Bull. Chem. Soc. Jpn., 1983, **56**, 1497 and US 4,521,589 describe the Grignard coupling of 2,5-dihalo-3-alkylthiophene in THF, wherein the alkyl group is lower alkyl with 1 to 4 C-atoms, like methyl. However, the resulting polymers are reported to have low molecular weight (1.370 or 2.300) and low regioregularity (as can be seen from the ¹H-NMR spectra). US 4,521,589 also mentions a higher weight fraction with a degree of polymerization of 96 as concluded from IR spectra, but no molecular weight measurement data are given. A series of publications by Elsenbaumer et al. also describes the synthesis of poly (3-alkyl thiophenes) by Grignard coupling (R. L. Elsenbaumer; K. Y. Jen; R. Oboodi, Synth. Met, 1986, 15, 169; furthermore K. Y. Jen; R. Oboodi; R. L. Elsenbaumer, Polym. Mater. Sci. Eng., 1985, 53, 79 and K.-Y. Jen; G. G. Miller; R. L. Elsenbaumer, J Chem Soc, Chem Commun, 1986, 1346). However, these polymers mostly have molecular weights (M_n) in the range of 3,000 to 8,000, with the exception of a homopolymer obtained from 2,5-diiodo-3,4dimethylthiophene and a copolymer obtained from 2,5-diiodo-3methyl- and 2,5-diiodo-3-n-butylthiophene, which are reported to have a molecular weight of 26,000 and 35,000 respectively. US

WO 2006/084545 PCT/EP2006/000360

- 5 -

4,711,742 (Elsenbaumer et al.) reports the synthesis of poly(3-butylthiophene) by Grignard coupling of the diiodo monomer in 2-methyl-tetrahydrofuran, giving a molecular weight of 41,400 corresponding to a degree of polymerization of 300. However, the poly (3-alkyl thiophenes) described in the above documents are regiorandom with relatively low amounts of the desired head-to-tail head-to-tail (HT-HT) triads (see e.g. K.-Y. Jen; G. G. Miller; R. L. Elsenbaumer, *J Chem Soc, Chem Commun*, 1986, 1346).

- In a study of poly (3-decyl thiophene) made by three different routes 10 (see P. C. Stein; C. Botta; A. Bolognesi; M. Catellani, Synth. Met, 1995, 69, 305) a sample prepared using the Grignard polymerisation of the diiodo monomer was found to have a regioregularity of 70% by ¹H-NMR. A study of the synthesis of poly (3-hexyl thiophene) using the Grignard reaction of 2,5-diiodo-3-hexylthiophene with 15 magnesium in ether (see H. Mao; S. Holdcroft, Macromolecules, 1992, 25, 554) resulted in a molecular weight (M_n) of 5,200. No direct regioregularity data are given but the ¹H-NMR shows peaks from all four possible triads, suggesting relatively low regionegularity. Another study of the same authors (see H. Mao; S. Holdcroft, 20 Macromolecules, 1993, 26, 1163) reported only poly (3-hexyl thiophenes) with low regioregularities (up to 58 % HT-HT triads or up to 80 % HT dyads).
- In conclusion, although the preparation of poly (3-alkyl thiophenes) by Grignard reaction with magnesium has been described in the literature, the polymers synthesised are reported to have low molecular weight and/or low or random regionegularity.
- Therefore, there is still a need for an improved method of preparing polymers, in particular poly-(3-substituted) thiophenes with high regioregularity, high molecular weight, high purity and high yields in an economical, effective and environmentally beneficial way, which is especially suitable for industrial large scale production.

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It was an aim of the present invention to provide an improved process for preparing polymers with these advantages, but not having the drawbacks of prior art methods mentioned above.

Other aims of the present invention are immediately evident to the person skilled in the art from the following detailed description.

The inventors of the present invention have found that these aims can be achieved, and the above problems be solved, by providing a process of preparing polymers, in particular poly-(3-substituted) thiophenes according to the present invention as described below. According to this process, a 3-substituted thiophene monomer with at least two groups, wherein these groups are leaving groups that are capable of reacting with magnesium, is reacted with magnesium in the presence of a catalytic amount of an organohalide or organomagnesium halide in a suitable solvent to form an intermediate, which is then polymerized in the presence of a suitable catalyst. It was surprisingly found that, by using this method it is possible to obtain polymers, in particular poly-(3-substituted) thiophenes, with high regioregularity, high molecular weight and high purity in good yields and avoiding large amounts of hazardous by-products that need to be eliminated.

The polymers prepared by the process according to the present invention are especially useful as charge transport materials for semiconductor or light-emitting materials, components or devices.

Summary of the Invention

The invention relates to a process of preparing a polymer from an optionally substituted thiophene having at least two groups that are capable of reacting with magnesium, by reacting said thiophene with magnesium in the presence of a catalytic amount of an organohalide or organomagnesium halide to form a regiochemical Grignard intermediate or a mixture of regiochemical Grignard intermediates,

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and polymerising said Grignard intermediate in the presence of a suitable catalyst.

The term "catalytic amount" as used above and below refers to an amount of organohalide or organomagnesium halide that is clearly below one equivalent of the other co-reagents like the thiophene monomer, preferably from > 0 to 0.5, very preferably from > 0 to 0.1, most preferably from > 0 to 0.05 equivalents of the thiophene monomer.

The invention further relates to a process as described above and below, wherein the thiophene is a 3-substituted soluble thiophene having groups in 2- and 5-position that are capable of reacting with magnesium.

The invention further relates to a process as described above and below, wherein the polymer is a regioregular head-to-tail (HT) polymer having a regioregularity of \geq 90 %, preferably \geq 95 %, very preferably \geq 98 %.

The invention further relates to a process as described above and below, by

- a) providing a suspension of magnesium in an organic solvent,
 preferably at room temperature or cooled to a temperature below room temperature,
- b) adding the thiophene having two groups that are capable of reacting with magnesium, optionally dissolved in a solvent or a mixture of solvents,
- c) adding the organohalide or organomagnesium halide in an amount from > 0 to 0.5 equivalents of the thiophene, so that said thiophene reacts with the magnesium to form a regiochemical Grignard intermediate or a mixture of regiochemical Grignard intermediates, and optionally adding further of the thiophene or thiophene solution,

- d) adding the catalyst, or adding the reaction mixture to the catalyst, and optionally agitating the resulting mixture, to form a polymer, and
- e) recovering the polymer from the mixture,

 wherein optionally the thiophene and the organohalide or
 organomagnesium halide are added together to the magnesium, i.e.
 steps b) and c) are combined, and
- wherein optionally step c) is carried out before step b), i.e. the
 organohalide or organomagnesium halide is added to the
 magnesium before the thiophene, and
 wherein in step d) optionally the reaction mixture is warmed to room
 temperature or a higher temperature before adding the catalyst.
- The invention further relates to novel polymers, in particular novel poly-3-substituted thiophenes, obtainable or obtained by a process as described above and below.
- The invention further relates to a semiconductor or charge transport material, component or device comprising one or more polymers as described above and below.
- The invention further relates to the use of polymers according to the invention as charge-transport, semiconducting, electrically conducting, photoconducting or light-emitting material in optical, electrooptical or electronic components or devices, organic field effect transistors (OFET), integrated circuitry (IC), thin film transistors (TFT), flat panel displays, radio frequency identification (RFID) tags, electroluminescent or photoluminescent devices or components, organic light emitting diodes (OLED), backlights of displays, photovoltaic or sensor devices, charge injection layers, Schottky diodes, planarising layers, antistatic films, conducting substrates or patterns, electrode materials in batteries, photoconductors, electrophotographic applications, electrophotographic recording,

organic memory devices, alignment layers, or for detecting and discriminating DNA sequences.

- The invention further relates to an optical, electrooptical or electronic device, FET, integrated circuit (IC), TFT, OLED or alignment layer comprising a semiconducting or charge transport material, component or device according to the invention.
- The invention further relates to a TFT or TFT array for flat panel
 displays, radio frequency identification (RFID) tag,
 electroluminescent display or backlight comprising a semiconducting
 or charge transport material, component or device or a FET, IC, TFT
 or OLED according to the invention.
- The invention further relates to a security marking or device comprising a FET or an RFID tag according to the invention.

Detailed Description of the Invention

The polymers prepared by the process according to the present invention are preferably selected of formula I

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wherein n is an integer > 1 and R¹ is a group that does not react with magnesium under the conditions as described for the process according to the present invention above and below. Preferably R¹ is an organic group which when it is unsubstituted and unmodified straight chained or branched alkyl has 5 or more C-atoms. Very preferably R¹ is an organic group having 5 or more C-atoms.

The thiophene used as educt in the process according to the present invention is preferably selected of formula II

$$X^{1}$$
 S
 X^{2}
 X^{2}

wherein R^1 has the meaning given in formula I and X^1 and X^2 are independently of each other a group that is capable of reacting with magnesium. Especially preferably X^1 and X^2 are CI and/or Br, most preferably Br.

The organohalide or organomagnesium halide used in the process according to the present invention is preferably an alkyl- or arylhalide of formula III

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$$R^3$$
-(Mg)- X^3 III

wherein

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is aryl or heteroaryl which is optionally substituted by one or more groups L, or straight chain, branched or cyclic alkyl with 1 to 20 C-atoms, which is optionally mono- or polysubstituted by F, Cl, Br or l, and wherein one or more non-adjacent CH₂ groups are optionally replaced, in each case independently from one another, by -O-, -S-, -NR⁰-, -SiR⁰R⁰⁰-, -CY¹=CY²- or -C≡C- in such a manner that O and/or S atoms are not linked directly to one another,

is F, Cl, Br, I or alkyl, alkoxy or thioalkyl with 1 to 20 C atoms, wherein one or more H atoms may be substituted by F or Cl,

 Y^1 and Y^2 are independently of each other H, F or CI,

WO 2006/084545 PCT/EP2006/000360

- 11 -

R⁰ and R⁰⁰ are independently of each other H, alkyl with 1 to 12 C-atoms or aryl,

X is Br, Cl or I, preferably Br.

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If R³ is aryl or heteroaryl it is preferably selected from phenyl, benzyl, fluorinated phenyl, pyridine, pyrimidine, biphenyl, naphthalene, thiophene, selenophene, fluorinated thiophene, benzo[1,2-b:4,5-b']dithiophene, thiazole and oxazole, all of which are unsubstituted, mono- or polysubstituted with L as defined above.

If R³ is an alkyl group it may be straight-chain or branched. It is preferably straight-chain, has 2, 3, 4, 5, 6, 7 or 8 carbon atoms and accordingly is preferably methyl, ethyl, propyl, butyl, pentyl, hexyl, heptyl, octyl, nonyl, decyl, undecyl, dodecyl, tridecyl, tetradecyl, or pentadecyl, for example.

If \mathbb{R}^3 is an alkyl group wherein one or more CH_2 groups are replaced by -CH=CH-, this may be straight-chain or branched. It is preferably straight-chain, has 2 to 10 C-atoms and accordingly is preferably vinyl, prop-1-, or prop-2-enyl, but-1-, 2- or but-3-enyl, pent-1-, 2-, 3- or pent-4-enyl, hex-1-, 2-, 3-, 4- or hex-5-enyl, hept-1-, 2-, 3-, 4-, 5- or hept-6-enyl, oct-1-, 2-, 3-, 4-, 5-, 6- or oct-7-enyl, non-1-, 2-, 3-, 4-, 5-, 6-, 7- or non-8-enyl, dec-1-, 2-, 3-, 4-, 5-, 6-, 7-, 8- or dec-9-enyl.

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R³ can also be a chiral group like for example 2-butyl (=1-methylpropyl), 2-methylbutyl, 2-methylpentyl, 3-methylpentyl, 2-ethylhexyl, 2-propylpentyl, 4-methylhexyl, 2-hexyl, 2-octyl, 2-nonyl, 2-decyl, 2-dodecyl, 1,1,1-trifluoro-2-octyl, 1,1,1-trifluoro-2-hexyl or an achiral branched group like for example isopropyl, isobutyl (=methylpropyl) or isopentyl (=3-methylbutyl).

Very preferably R³ is straight-chain or branched alkyl or alkenyl with 1 to 12 C atoms, phenyl or benzyl.

Especially suitable and preferred organohalides are for example methyl bromide, ethyl bromide, isopropyl bromide, vinyl bromide and benzyl bromide.

- The organohalide or organomagnesium halide is preferably added in an amount from 0.001 to 0.1, very preferably from 0.01 to 0.05 equivalents of the thiophene monomer.
- The process according to the present invention offers significant advantages over the methods disclosed in prior art especially regarding economical and ecological aspects, whilst providing polythiophenes in comparable or even better yield and quality.
- With the process according to the present invention it is possible to prepare polythiophenes, in particular HT-poly-(3-substituted) thiophenes with a regioregularity of 90 % or higher in a yield of 50 % or higher (related to the thiophene educt). As mentioned above, these highly regioregular HT-poly-(3-substituted) thiophenes are particularly suitable for use as charge-transport or semiconductor material in electronic or optical devices.

The regioregular polymers of the present invention thus have a high number, and do preferably exclusively consist, of HT-linked repeating units as shown in formula la

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Furthermore, the process according to the present invention is costeffective and safe and in particular has the following advantages:

 Only a small amount of alkyl halide byproduct is generated. This is advantageous because the alkyl halide byproduct can interfere

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with the polymerisation causing undesired endcapping and lower molecular weights. Also, the emission of large amounts of hazardous by-products like methyl bromide can be avoided

- Magnesium metal can be used directly, rather than air sensitive solutions of preformed alkyl grignards. Moreover, the reaction can also be run in cyclic ethers like THF instead of diethyl ether.
- The Grignard reaction can be run at low temperatures. This allows the inclusion of sensitive functionalities onto the thiophene monomer.

After polymerisation the polymer is preferably recovered from the reaction mixture, for example by conventional work-up, and purified. This can be achieved according to standard methods known to the expert and described in the literature.

As a result of the process according to the present invention, the obtained polythiophenes are usually terminated by the leaving groups that are capable of reacting with magnesium in 2 and 5-position of the thiophene monomer, or derivatives thereof. In case thiophene educts of formula II are used, the obtained polymers correspond to formula I1

wherein n, R^1 , X^1 and X^2 have the meanings given in formula I and II.

In another preferred embodiment of the present invention the terminal groups of the polymer are chemically modified ('endcapped') during or after polymerisation.

Endcapping can be carried out before or after recovering the polymer from the polymerisation reaction mixture, before or after work-up of

WO 2006/084545 PCT/EP2006/000360

the polymer or before or after its purification, depending on which is more suitable and more effective regarding the material costs, time and reaction conditions involved. For example, in case expensive coreactants are used for endcapping it may be more economical to carry out the endcapping after purification of the polymer. In case the purification effort is economically more important than the coreactants it may be preferred to carry out the endcapping before purification or even before recovering the polymer from the polymerisation reaction mixture.

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As a result of the process according to the present invention, at the end of the polymerisation step the end groups X^1 and X^2 are either a halogen or Grignard group. Also, small amounts of endgroups R^3 can be present as a result of a reaction with the byproduct R^3X^3 from the preparation of the thiophene intermediate. For endcapping, typically an aliphatic Grignard reagent RMgX or dialkyl Grignard reagent MgR₂, wherein X is halogen and R is an aliphatic group, or active magnesium is added to convert the remaining halogen end groups to Grignard groups. Subsequently, for example to give an alkyl end group an excess of an ω -haloalkane is added which will couple to the Grignard. Alternatively, to give a proton end group the polymerisation is quenched into a non-solvent such as an alcohol.

To provide reactive functional end groups, like for example hydroxyl or amine groups or protected versions thereof, the halogen end groups are for example reacted with a Grignard reagent R'MgX, wherein R' is such a reactive functional group or protected reactive functional group.

30 Instead of a Grignard reagent it is also possible to carry out endcapping using an organo lithium reagent, followed by addition of an ω-haloalkane.

It is also possible to replace H end groups by reactive functional groups by using e.g. the methods described in US 6,602,974, such

as a Vilsmeier reaction to introduce aldehyde groups followed by reduction with metal hydrides to form hydroxyl groups.

If the polymer has been fully worked up prior to endcapping, it is preferred to dissolve the polymer in a good solvent for Grignard coupling such as diethyl ether or THF. The solution is then treated for example with the above mentioned organo Grignard reagent RMgX or MgR₂ or R'MgX or with a zinc reagent, RZnX, R'ZnX or ZnR₂, where R and R' are as defined above. A suitable nickel or palladium catalyst is then added along with the haloalkane.

Very preferred are endcapped polymers wherein the terminal groups during or after polymerisation are replaced by H or an alkyl group (hereinafter also referred to as 'polymers endcapped by H or an alkyl group').

Preferably endcapping is carried out before purification of the polymer. Further preferably endcapping is carried out after step d) of the process as described above and below. In another preferred embodiment of the present invention the endcapper is added during polymerisation to remove the end groups and possibly control the molecular weight of the polymer.

Preferably, substantially all molecules in a polymer sample are endcapped in accordance with this invention, but at least 80 %, preferably at least 90 %, most preferably at least 98 % are endcapped.

By chemical modification of the terminal groups (endcapping) of the polymers according to the present invention, it is possible to prepare novel polymers with different terminal groups. These polymers are preferably selected of formula I2

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$$X^{11} = \begin{bmatrix} R^1 \\ S \end{bmatrix}_{n} X^{22}$$

wherein n and R^1 have the meanings given in formula I and II, and X^{11} and X^{22} are independently of each other H, halogen, stannate, boronate or an aliphatic, cycloaliphatic or aromatic group that may also comprise one or more hetero atoms.

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Especially preferably X^{11} and X^{22} are selected from H or straight-chain or branched alkyl with 1 to 20, preferably 1 to 12, very preferably 1 to 6 C-atoms, most preferably straight-chain alkyl or branched alkyl like isopropyl or tert. butyl. Aromatic groups X^{11} and X^{22} tend to be bulky and are less preferred.

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As described above, the end groups X^{11} and X^{22} are preferably introduced by reacting the polymer of formula I1 with a Grignard reagent MgRX, MgR₂ or MgR'X as described above, wherein R and R' are X^{11} or X^{22} as defined in formula I2.

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By introducing suitable functional end groups X¹¹ and/or X²² it is possible to prepare block copolymers from the polymers according to the present invention. For example, if one or both of the end groups X¹¹ and X²² in a polymer of formula I2 is a reactive group or a protected reactive group, like for example an optionally protected hydroxy or amine group, they can be reacted (after removing the protective group) with the end group of another polymer of formula I2 (e.g. with different groups R¹ and/or X¹¹ and/or X²²), or with a polymer of different structure. If one of X¹¹ and X²² is a reactive group, diblock copolymers can be formed. If both X¹¹ and X²² are reactive groups, a triblock copolymer can be formed.

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Alternatively a block copolymer can be formed by introducing reactive or protected reactive groups X¹¹ and/or X²², adding a

catalyst and one or monomers, and initiating a new polymerization reaction starting from the site of the groups X^{11} and/or X^{22} .

Suitable functional end groups and methods of their introduction can be taken from the above disclosure and from prior art. Details how to prepare block copolymers can also be taken e.g. from US 6,602,974.

The process according to the present invention is exemplarily illustrated in Scheme 1 below, wherein n, R^1 , R^3 , X^1 , X^2 and X^3 have the meaning of formula I, II and III.

Scheme 1

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$$X^{1} \xrightarrow{S} X^{2} \xrightarrow{\text{THF}} X^{1} \text{Mg} \xrightarrow{X^{1} \text{Mg}} S X^{2} \xrightarrow{\text{Ni(dppp)Cl}_{2}} X^{1} \text{Mg} \xrightarrow{X^{1} \text{Mg}} S X^{2} \xrightarrow{\text{Ni(dppp)Cl}_{2}} X^{2} \xrightarrow{\text{Ni$$

- 20 R³X³ is preferably an organohalide like e.g. MeBr, i-PropBr, EtBr added in a catalytic amount, preferably 0.01 to 0.05 equivalents of (1). If R¹ is a group that is reactive with magnesium under the process conditions as described above and below, it is preferably transformed into, or coupled with, a protective group, in order not to take part in the reactions forming (2) and (3). Suitable protective groups are known to the expert and described in the literature, for example in Greene and Greene, "Protective Groups in Organic Synthesis", John Wiley and Sons, New York (1981).
- The starting materials and reagents used in the process according to the present invention are either commercially available (e.g. from Aldrich) or can be easily synthesized by methods well known to those skilled in the art.
- In some cases it may be suitable to further purify the thiophene monomer and the other reagents before using them in the inventive

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process. Purification can be carried out by standard methods known to the expert and described in the literature.

The process according to the present invention as exemplarily depicted in Scheme 1 is preferably carried out as follows:

In a first step (a) a suspension of magnesium in a solvent like e.g. THF or a solvent mixture is provided, for example at room temperature (RT) or slightly above, preferably cooled to a temperature below RT, very preferably below +5°C, most preferably below 0°C, epecially 0 to -5°C. The magnesium is provided in an at least molar amount of the thiophene educt (1), preferably in an excessive amount from more than 1 to 3, preferably from 1.01 to 2.00, very preferably from 1.02 to 1.50, most preferably from 1.02 to 1.20 times the molar amount of the thiophene educt (1).

In a second step (b) a 3-substituted thiophene (1), preferably 3-substituted 2,5-dihalothiophene, most preferably 3-substituted 2,5-dibromothiophene, like for example 2,5-dibromo-3-alkylthiophene, preferably dissolved in a solvent like THF or a solvent mixture, is added to the magnesium suspension while keeping the temperature at or below RT, preferably below +5°C.

The solvent or solvent mixture preferably consists of one or more polar aprotic solvents, which can be any solvent of this type, like for example dialkylethers such as diethyl ether, di-n-butyl ether, di-n-propyl ether, di-isopropyl ether, glycol ethers such as 1,2-dimethoxyethane, ethers with two different alkyl groups such as tert-butylmethyl ether, cyclic ethers like tetrahydrofuran (THF), 2-methyl tetrahydrofuran, tetrahydropyran or 1,4-dioxan, or mixtures of these colvents, or mixtures of aromatic or aliphatic solvents such as mixtures of toluene with the above ethers.

Preferably the solvent is selected from cyclic ethers, especially preferably from THF or 2-methyltetrahydrofuran.

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The concentration of the thiophene educt (1) in the solvent is preferably from 40 to 200 g/l, very preferably from 80 to 130 g/l.

In the next step (step c)), a catalytic amount of an organohalide or organomagnesium halide, preferably or formula III, which is optionally dissolved in an organic solvent like THF, is added to the reaction mixture, preferably in an amount from 0.01 to 0.05 equivalents of thiophene. This starts the Grignard reaction. The reaction mixture is optionally stirred or otherwise agitated, preferably 10 at a temperature from -5 to +5°C, until all the magnesium is consumed, to give the intermediate (2).

It is also possible to combine steps b) and c) by adding a solution containing both the thiophene and the organohalide or organomagnesium halide to the magnesium suspension, preferably over a longer time interval (e.g. several hours) depending on the total amount of reagents.

It is also possible to carry out step c) before step b), i.e. first adding the organohalide or organomagnesium halide, and then adding the thiophene or thiophene solution.

The total amount of thiophene is approximately 1 equivalent or less of the magnesium. It is possible to add the complete amount of thiophene to the reaction mixture in one portion in step b). In a preferred embodiment, however, only a small portion of the total amount of thiophene or thiophene solution is added to the reaction mixture in step b), preferably in an amount of > 0 to 50 mol %, very preferably 1 to 50 mol %, most preferably 5 to 20 % of the magnesium. Then the organohalide or organomagnesium halide is added as described in step c) to start the Grignard reaction. The reaction mixture is optionally stirred or otherwise agitated, preferably at a temperature from -5 to +5°C, whilst the remainder of the thiophene or thiophene solution is added. Stirring or agitation is continued, preferably at a temperature from -5 to +5°C until all the magnesium is consumed, to give the intermediate (2).

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In an optional next step the non-reacted magnesium is then removed from the reaction mixture e.g. by filtration. Preferably the magnesium is removed. The solution can be warmed to RT or a temperature above room temperature prior to the magnesium removal.

In the next step (d), the reaction mixture is warmed to RT or a temperature above RT, and a suitable catalyst is added to the reaction mixture in an effective amount to initiate the polymerisation via a Grignard metathesis reaction. Usually the catalyst is reactive enough to start the polymerisation without other means, however in practice the mixture is typically stirred while adding the catalyst. The polymerisation cross-coupling reaction is then allowed to proceed, optionally under agitating and/or heating the reaction mixture, for example heating to reflux, for a sufficient period of time to give the polymer (3).

Alternatively, it is also possible to add the reaction mixture to the catalyst.

The catalyst in step d) can be any catalyst that is suitable for a reaction involving organometallic reagents, including for example Ni, Pd or other transition metal catalysts. Preferably it is selected from nickel catalysts, in particular Ni(II) catalysts like Ni(dppp)Cl₂ (1,3-diphenylphosphinopropane nickel(II) chloride) or Ni(dppe)Cl₂ (1,2-bis(diphenylphosphino)ethane nickel(II) chloride), furthermore e.g. copper catalysts like CuI, CuBr or Li₂CuCl₄ or Pd catalysts like Pd(PPh₃), PdCl₂(dppe), PdCl₂(dppf) or iron catalysts like Fe(acac)₃.

The catalyst is preferably added in an amount from 0.1 to 5 %, preferably 0.5 to 2 mol % of the thiophene educt.

The process according to the present invention may be run at any temperature providing a sufficient conversion rate. It is preferred that the reaction is performed at a temperature between -5 °C and the solvent's reflux temperature, in particular at the temperatures as

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specified above and below. The term "reflux temperature" includes temperatures at or slightly below the boiling point of the solvent.

The selection of a suitable reaction time depends on the actual rate of the individual reaction. Preferably the reaction times are as given above and below.

For the reaction of the thiophene educt with magnesium (step c)) the reaction temperature is preferably in the range from +5 to -5°C, most preferably from 0 to -5°C. The reaction time is from 15 min to 24 h, preferably from 30 min to 6 h.

For the polymerisation reaction (step d)) the temperature is preferably in the range from -5 °C to reflux temperature, most preferably from room temperature to reflux temperature. The reaction time is from 15 min to 48 h, preferably from 45 min to 4h.

The steps b), c) and d) are optionally carried out under agitating the reaction mixture, which can be achieved by known methods.

Steps a) to d), in particular steps c) and d) are preferably carried out under a dry and inert atmosphere, e.g. under nitrogen.

The reaction products (2) and (3) prepared by the process according to the present invention may be isolated by usual work-up and purification with standard procedures well known to those skilled in the art.

The intermediate (2) obtained in step b) is directly used in step d).

However, for the purpose of e.g. investigating the proceeding of the reaction process or analysing the ratio of the regiochemical intermediates produced it may be suitable to quench the reaction mixture.

In the next step (e) the polymer (3) is recovered from the reaction mixture. Preferably the polymer is recovered from the mixture by

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quenching the reaction mixture with an alcoholic or aqueous solution or/and precipitating the polymer.

The polymer can then be purified by known methods to remove inorganic impurities as well as monomers and short-chain oligomers, or may also be used without further purification. Preferably the polymer is purified. Suitable and preferred purification methods include solid-phase extraction, liquid-liquid extraction, precipitation, adsorption and filtration. Preferably a combination of purification methods is selected to obtain a high-purity product best suitable for application,

For example a preferred purification method includes aqueous quenching, for example with a mixture of chloroform/water, optional liquid/liquid extraction or distilling off the original solvent, precipitation into a polar solvent like for example methanol, and washing with an unpolar solvent like for example heptane.

Suitable reagents and process conditions for the steps d) and e) including the reaction of the intermediate (2) to the polymer (3), can also be taken from the literature.

The intermediate (2) is usually obtained as a mixture of regiochemical isomers (2a) and (2b), and may also include a, typically small, amount of the double-Grignard product (2c), as shown below, wherein X^1 , X^2 and R^1 have the meanings of formula I and I1

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$$X^{1}Mg$$
 X^{2} $X^{1}Mg$ X^{2} $X^{1}Mg$ X^{2} $X^{1}Mg$ X^{2} X^{2} $X^{1}Mg$ X^{2} X^{2}

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The ratio of these intermediates is depending for example on the molar excess of Magnesium, the solvent, temperature and reaction time.

- For example, if the reaction is carried out according to the especially preferred embodiment described above, the intermediates 2a, 2b and 2c can be obtained in a ratio of 85/5/10.
- Depending on the processing conditions, like for example the solvent and the amount of magnesium, the ratio of isomer intermediates 2a/2b/2c can be varied. A preferred process includes isomer intermediate ratios 2a/2b/2c of 80-90/2-20/0-20.
- The polymers according to the present invention are especially preferably regionegular HT-poly-(3-substituted) thiophenes. The regionegularity (=head-to-tail couplings divided by the total couplings, and expressed as a percentage), in these polymers is preferably at least 85 %, in particular 90% or more, very preferably 95% or more, most preferably from 98 to 100%.

Polymers of formula I, I1 and I2 having a high percentage of HT-couplings accordingly have a corresponding high number of HT dyads or HT-HT-triads formula la/b, I1a/b and I2a/b shown below.

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$$R^{1}$$

$$R^{1}$$
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$$\begin{array}{c} R^1 \\ S \\ S \\ \end{array}$$
 Ib

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$$R^1$$
 S R^1 R^1 R^2 R^2 R^3 R^4 R^4 R^4 R^4 R^4

$$X^{11}$$
 S
 R^1
 S
 R^1
 R^2
 R^2
 R^2
 R^2
 R^2
 R^2

wherein R^1 , X^1 , X^2 , X^{11} , X^{22} have the meanings given above.

- Regioregular poly-(3-substituted) thiophenes are advantageous as they show strong interchain pi-pi-stacking interactions and a high degree of crystallinity, making them effective charge transport materials with high carrier mobilities.
- The polymers according to the present invention preferably have a degree of polymerisation (or number n of recurring units) from 2 to

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5,000, in particular from 10 to 5,000 or from 110 to 5,000, very preferably from 50 to 1,000, most preferably from above 100 to 1,000.

- Further preferred are polymers having a molecular weight from 5,000 to 300,000, in particular from 10,000 to 100,000, preferably from 15,000 to 100,000, very preferably from 20,000 to 100,000.
- R¹ in formula I, I1 and II is preferably an organic group, preferably a non-reactive or protected reactive organic group, which has preferably 5 or more C-atoms.

Especially preferably R¹ is straight chain, branched or cyclic alkyl with 1 or more, preferably 5 or more, very preferably 1 to 20 C-atoms, which may be unsubstituted, mono- or poly-substituted by F, CI, Br or I, wherein one or more non-adjacent CH₂ groups are optionally replaced, in each case independently from one another, by -O-, -S-, -NR⁰-, -SiR⁰R⁰⁰-, -CY¹=CY²- or -C≡C- in such a manner that O and/or S atoms are not linked directly to one another, optionally substituted aryl or heteroaryl preferably having 1 to 30 C-atoms, or P-Sp, with

R⁰ and R⁰⁰ being independently of each other H or alkyl with 1 to 12 C-atoms,

Y¹ and Y² being independently of each other H, F or CI,

P being a polymerisable or reactive group which is optionally protected, and

Sp being a spacer group or a single bond.

 X^1 and X^2 in formula I1 and II are preferably independently of each other selected from halogen, very preferably CI or Br, most preferably Br.

X¹¹ and X²² in formula I2 are preferably independently of each other selected from H, halogen, B(OR')(OR") or SnR⁰R⁰⁰R⁰⁰⁰ or straight chain, branched or cyclic alkyl with 1 to 20 C-atoms, which may be unsubstituted, mono- or poly-substituted by F, Cl, Br, I, -CN and/ or -OH, it being also possible for one or more non-adjacent CH₂ groups to be replaced, in each case independently from one another, by -O-, -S-, -NH-, -NR⁰-, -SiR⁰R⁰⁰-, -CO-, -COO-, -OCO-O-, -S-CO-, -CO-S-, -CY¹=CY²- or -C≡C- in such a manner that O and/or S atoms are not linked directly to one another, optionally substituted aryl or heteroaryl, or P-Sp, with R⁰, R⁰⁰, Y¹, Y², P and Sp having the meanings given above,

R⁰⁰⁰ being H or alkyl with 1 to 12 C-atoms, and

15 R' and R" being independently of each other H or alkyl with 1 to 12 C-atoms, or OR' and OR" together with the boron atom may also form a cyclic group having 2 to 10 C atoms.

Especially preferred are polymers and compounds of formula I, II, I1 and I2 wherein

- R¹ is an organic group, preferably an alkyl group with 5 or more C-atoms,
- R¹ is a straight-chain alkyl group with 1 to 12, preferably 5 to 12 C-atoms,
 - R¹ is n-hexyl,

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- R¹ is selected from C₁-C₂₀-alkyl that is optionally substituted with one or more fluorine atoms, C₁-C₂₀-alkenyl, C₁-C₂₀-alkynyl, C₁-C₂₀-alkoxy, C₁-C₂₀-thioalkyl, C₁-C₂₀-silyl, C₁-C₂₀-amino, C₁-C₂₀-fluoroalkyl, optionally substituted aryl or heteroaryl, or P-Sp-, in particular C₁-C₂₀-alkyl or C₁-C₂₀-fluoroalkyl, preferably straight-chain groups,
 - R¹ is selected from alkyl that is optionally substituted with one or more fluorine atoms, alkenyl, alkynyl, alkoxy, thioalkyl or

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fluoroalkyl, all of which are straight-chain and have 1 to 12, preferably 5 to 12 C-atoms,

- R¹ is selected from pentyl, hexyl, heptyl, octyl, nonyl, decyl, undecyl or dodecyl,
- X¹ and X² have the same meaning,
- X¹ and X² denote Br,
- X¹¹ and X²² have the same meaning,
- 10 X^{11} and X^{22} denote H,
 - X¹¹ and X²² are selected from alkyl that is optionally substituted with one or more fluorine atoms, alkenyl, alkynyl, alkoxy, thioalkyl, silyl, ester, amino or fluoroalkyl, all of these groups being straight-chain or branched and having 1 to 20, preferably 1 to 12, most preferably 1 to 6 C atoms, or optionally substituted aryl or heteroaryl, or P-Sp as defined above, in particular straight-chain or branched C₁-C₆-alkyl, most preferably isopropyl, tert.butyl, or 2-methylbutyl,
 - n is an integer from 2 to 5000, in particular 50 to 1000.

If in formula I, II, I1 and I2 R¹ is an alkyl or alkoxy radical, i.e. where the terminal CH₂ group is replaced by -O-, this may be straight-chain or branched. It is preferably straight-chain, has 2 to 8 carbon atoms and accordingly is preferably ethyl, propyl, butyl, pentyl, hexyl, heptyl, octyl, ethoxy, propoxy, butoxy, pentoxy, hexyloxy, heptoxy, or octoxy, furthermore methyl, nonyl, decyl, undecyl, dodecyl, tridecyl, tetradecyl, pentadecyl, nonoxy, decoxy, undecoxy, dodecoxy, tridecoxy or tetradecoxy, for example. Especially preferred are n-hexyl and n-dodecyl.

If in formula I, II, I1 and I2 R¹ is oxaalkyl, i.e. where one CH₂ group is replaced by -O-, is preferably straight-chain 2-oxapropyl (=methoxymethyl), 2- (=ethoxymethyl) or 3-oxabutyl (=2-methoxyethyl), 2-, 3-, or 4-oxapentyl, 2-, 3-, 4-, or 5-oxahexyl, 2-, 3-, 4-, 5-, or 6-oxaheptyl, 2-, 3-, 4-, 5-, 6- or 7-oxaoctyl, 2-, 3-, 4-, 5-, 6-, 7- or 8-oxanonyl or 2-, 3-, 4-, 5-, 6-, 7-, 8- or 9-oxadecyl, for example.

If in formula I, II and I1 R¹ is thioalkyl, i.e where one CH₂ group is replaced by –S-, is preferably straight-chain thiomethyl (-SCH₃), 1-thioethyl (-SCH₂CH₃), 1-thiopropyl (= -SCH₂CH₂CH₃), 1-(thiobutyl), 1-(thiopentyl), 1-(thiohexyl), 1-(thiohexyl), 1-(thiodecyl), 1-(thiodecyl), wherein preferably the CH₂ group adjacent to the sp² hybridised vinyl carbon atom is replaced.

- If in formula I, II, I1 and I2 R^1 is fluoroalkyl, it is preferably straight-chain perfluoroalkyl C_iF_{2i+1} , wherein i is an integer from 1 to 15, in particular CF_3 , C_2F_5 , C_3F_7 , C_4F_9 , C_5F_{11} , C_6F_{13} , C_7F_{15} or C_8F_{17} , very preferably C_6F_{13} .
- $-CY^1=CY^2$ is preferably -CH=CH-, -CF=CF- or -CH=C(CN)-.

Aryl and heteroaryl preferably denote a mono-, bi- or tricyclic aromatic or heteroaromatic group with up to 25 C atoms that may also comprise condensed rings and is optionally substituted with one or more groups L, wherein L is halogen or an alkyl, alkoxy, alkylcarbonyl or alkoxycarbonyl group with 1 to 12 C atoms, wherein one or more H atoms may be replaced by F or CI.

- Especially preferred aryl and heteroaryl groups are phenyl in which, in addition, one or more CH groups may be replaced by N, naphthalene, thiophene, thienothiophene, dithienothiophene, alkyl fluorene and oxazole, all of which can be unsubstituted, mono- or polysubstituted with L as defined above.
- Another preferred embodiment of the present invention relates to polythiophenes that are substituted in 3-position with a polymerisable or reactive group, which is optionally protected during the process of forming the polythiophene. Particular preferred polymers of this type are those of formula I, I1 or I2 wherein R¹ denotes P-Sp. These polymers are particularly useful as semiconductors or charge transport materials, as they can be crosslinked via the groups P, for

example by polymerisation in situ, during or after processing the polymer into a thin film for a semiconductor component, to yield crosslinked polymer films with high charge carrier mobility and high thermal, mechanical and chemical stability.

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Preferably the polymerisable or reactive group P is selected from

 $CH_2=CW^1-COO-$, $CH_2=CW^1-CO-$, W^2HC CH-

-N W8

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V² (CH₂)_{k1}-O-, CH₂=CW²-(O)_{k1}-, CH₃-CH=CH-O-

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 $(CH_2=CH)_2CH-OCO-, (CH_2=CH-CH_2)_2CH-OCO-, (CH_2=CH)_2CH-O-, (CH_2=CH-CH_2)_2N-, (CH_2=CH-CH_2)_2N-CO-, HO-CW^2W^3-, HS-CW^2W^3-, HW^2N-, HO-CW^2W^3-NH-, CH_2=CW^1-CO-NH-, CH_2=CH-(COO)_{k1}-$

Phe- $(O)_{k2}$ -, CH_2 =CH- $(CO)_{k1}$ -Phe- $(O)_{k2}$ -, Phe-CH=CH-, HOOC-, OCN-, and W⁴W⁵W⁶Si-, with W¹ being H, CI, CN, CF₃, phenyl or alkyl with 1 to 5 C-atoms, in particular H, CI or CH_3 , W² and W³ being independently of each other H or alkyl with 1 to 5 C-atoms, in

particular H, methyl, ethyl or n-propyl, W⁴, W⁵ and W⁶ being independently of each other Cl, oxaalkyl or oxacarbonylalkyl with 1 to 5 C-atoms, W⁷ and W⁸ being independently of each other H, Cl or alkyl with 1 to 5 C-atoms, Phe being 1,4-phenylene that is optionally substituted by one or more groups L as defined above, and k₁ and k₂

being independently of each other 0 or 1,

or a protected derivative of these groups which is non-reactive with magnesium under the conditions described for the process according to the present invention. Suitable protective groups are known to the expert and described in the literature, for example in Greene and Greene, "Protective Groups in Organic Synthesis", John Wiley and Sons, New York (1981), like for example acetals or ketals.

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Preferably, however, the polymerisable group is added to the inventive polymers as the last step, after polymerisation.

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Especially preferred groups P are CH₂=CH-COO-, CH₂=C(CH₃)-COO-, CH₂=CH-, CH₂=CH-O-, (CH₂=CH)₂CH-OCO-, (CH₂=CH)₂CH-OCO-

Polymerisation of group P can be carried out according to methods that are known the expert and described in the literature, for example in D. J. Broer; G. Challa; G. N. Mol, *Macromol. Chem*, 1991, **192**, 59.

As spacer group Sp all groups can be used that are known for this purpose to the skilled in the art. The spacer group Sp is preferably of formula Sp'-X', such that P-Sp- is P-Sp'-X'-, wherein

sp' is alkylene with up to 30 C atoms which is unsubstituted or mono- or polysubstituted by F, Cl, Br, I or CN, it being also possible for one or more non-adjacent CH₂ groups to be replaced, in each case independently from one another, by -O-, -S-, -NH-, -NR⁰-, -SiR⁰R⁰⁰-, -CO-, -COO-, -OCO-, -OCO-O-, -S-CO-, -CO-S-, -CH=CH- or -C≡C- in such a manner that O and/or S atoms are not linked directly to one another,

R⁰ and R⁰⁰ are independently of each other H or alkyl with 1 to 12 C-atoms, and

 Y^1 and Y^2 are independently of each other H, F, Cl or CN.

X' is preferably -O-, -S-, -OCH₂-, -CH₂O-, -SCH₂-, -CH₂S-, -CF₂O-, -OCF₂-, -CF₂S-, -SCF₂-, -CH₂CH₂-, -CF₂CH₂-, -CH₂CF₂-, -CF₂CF₂-, -CH=N-, -N=N-, -N=N-, -CH=CR⁰-, -CY¹=CY²-, -C \equiv C- or a single bond, in particular -O-, -S-, -C \equiv C-, -CY¹=CY²- or a single bond. In another preferred embodiment X' is a group that is able to form a conjugated system, such as -C \equiv C- or -CY¹=CY²-, or a single bond.

Typical groups Sp' are, for example, -(CH₂)_p-, -(CH₂CH₂O)_q-CH₂CH₂-, -CH₂CH₂-S-CH₂CH₂- or -CH₂CH₂-NH-CH₂CH₂- or -(SiR⁰R⁰⁰-O)_p-, with p being an integer from 2 to 12, q being an integer from 1 to 3 and R⁰ and R⁰⁰ having the meanings given above.

Preferred groups Sp' are ethylene, propylene, butylene, pentylene, hexylene, heptylene, octylene, nonylene, decylene, undecylene, dodecylene, octadecylene, ethyleneoxyethylene, methyleneoxybutylene, ethylene-thioethylene, ethylene-N-methyliminoethylene, 1-methylalkylene, ethenylene, propenylene and butenylene for example.

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The polymers of the present invention are useful as optical, electronic and semiconductor materials, in particular as charge transport materials in field effect transistors (FETs), e.g., as components of integrated circuitry, ID tags or TFT applications. Alternatively, they may be used in organic light emitting diodes (OLEDs) in electroluminescent display applications or as backlight of, e.g., liquid crystal displays, as photovoltaics or sensor materials, for electrophotographic recording, and for other semiconductor applications.

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The polymers according to the present invention show especially advantageous solubility properties which allow production processes using solutions of these compounds. Thus films, including layers and coatings, may be generated by low cost production techniques, e.g., spin coating. Suitable solvents or solvent mixtures comprise alkanes

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WO 2006/084545

and/ or aromatics, especially their fluorinated or chlorinated derivatives.

PCT/EP2006/000360

The polymers of the present invention are especially useful as charge transport materials in FETs. Such FETs, where an organic semiconductive material is arranged as a film between a gatedielectric and a drain and a source electrode, are generally known, e.g., from US 5,892,244, WO 00/79617, US 5,998,804, and from the references cited in the background and prior art chapter and listed 10 below. Due to the advantages, like low cost production using the solubility properties of the compounds according to the invention and thus the processibility of large surfaces, preferred applications of these FETs are such as integrated circuitry, TFT-displays and security applications.

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In security applications, field effect transistors and other devices with semiconductive materials, like transistors or diodes, may be used for ID tags or security markings to authenticate and prevent counterfeiting of documents of value like banknotes, credit cards or ID cards, national ID documents, licenses or any product with money value, like stamps, tickets, shares, cheques etc..

Alternatively, the polymers according to the invention may be used in organic light emitting devices or diodes (OLEDs), e.g., in display applications or as backlight of e.g. liquid crystal displays. Common OLEDs are realized using multilayer structures. An emission layer is generally sandwiched between one or more electron-transport and/ or hole-transport layers. By applying an electric voltage electrons and holes as charge carriers move towards the emission layer where their recombination leads to the excitation and hence luminescence of the lumophor units contained in the emission layer. The inventive compounds, materials and films may be employed in one or more of the charge transport layers and/ or in the emission layer, corresponding to their electrical and/ or optical properties. Furthermore their use within the emission layer is especially

advantageous, if the polymers according to the invention show

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electroluminescent properties themselves or comprise electroluminescent groups or compounds. The selection, characterization as well as the processing of suitable monomeric, oligomeric and polymeric compounds or materials for the use in OLEDs is generally known by a person skilled in the art, see, e.g., Meerholz, Synthetic Materials, 111-112, 2000, 31-34, Alcala, J. Appl. Phys., 88, 2000, 7124-7128 and the literature cited therein.

According to another use, the polymers according to the present invention, especially those which show photoluminescent properties, may be employed as materials of light sources, e.g., of display devices such as described in EP 0 889 350 A1 or by C. Weder et al., Science, 279, 1998, 835-837.

A further aspect of the invention relates to both the oxidised and reduced form of the polymers according to this invention. Either loss or gain of electrons results in formation of a highly delocalised ionic form, which is of high conductivity. This can occur on exposure to common dopants. Suitable dopants and methods of doping are known to those skilled in the art, e.g., from EP 0 528 662, US 5,198,153 or WO 96/21659.

The doping process typically implies treatment of the semiconductor material with an oxidating or reducing agent in a redox reaction to form delocalised ionic centres in the material, with the corresponding counterions derived from the applied dopants. Suitable doping methods comprise for example exposure to a doping vapor in the atmospheric pressure or at a reduced pressure, electrochemical doping in a solution containing a dopant, bringing a dopant into contact with the semiconductor material to be thermally diffused, and ion-implantantion of the dopant into the semiconductor material.

When electrons are used as carriers, suitable dopants are for example halogens (e.g., I₂, Cl₂, Br₂, ICl, ICl₃, IBr and IF), Lewis acids (e.g., PF₅, AsF₅, SbF₅, BF₃, BCl₃, SbCl₅, BBr₃ and SO₃), protonic acids, organic acids, or amino acids (e.g., HF, HCl, HNO₃, H₂SO₄,

WO 2006/084545 PCT/EP2006/000360

HClO₄, FSO₃H and ClSO₃H), transition metal compounds (e.g., FeCl₃, FeOCl, Fe(ClO₄)₃, Fe(4-CH₃C₆H₄SO₃)₃, TiCl₄, ZrCl₄, HfCl₄, NbF₅, NbCl₅, TaCl₅, MoF₅, MoCl₅, WF₅, WCl₆, UF₆ and LnCl₃ (wherein Ln is a lanthanoid), anions (e.g., Cl⁻, Br⁻, l⁻, l₃⁻, HSO₄⁻, SO₄²⁻, NO₃⁻, ClO₄⁻, BF₄⁻, PF₆⁻, AsF₆⁻, SbF₆⁻, FeCl₄⁻, Fe(CN)₆³⁻, and anions of various sulfonic acids, such as aryl-SO₃⁻). When holes are used as carriers, examples of dopants are cations (e.g., H⁺, Li⁺, Na⁺, K⁺, Rb⁺ and Cs⁺), alkali metals (e.g., Li, Na, K, Rb, and Cs), alkaline-earth metals (e.g., Ca, Sr, and Ba), O₂, XeOF₄, (NO₂⁺) (SbF₆⁻), (NO₂⁺) (SbCl₆⁻), (NO₂⁺) (BF₄⁻), AgClO₄, H₂IrCl₆, La(NO₃)₃ · 6H₂O, FSO₂OOSO₂F, Eu, acetylcholine, R₄N⁺, (R is an alkyl group), R₄P⁺ (R is an alkyl group), R₆As⁺ (R is an alkyl group), and R₃S⁺ (R is an alkyl group).

The conducting form of the polymers of the present invention can be used as an organic "metal" in applications, for example, but not limited to, charge injection layers and ITO planarising layers in organic light emitting diode applications, films for flat panel displays and touch screens, antistatic films, printed conductive substrates, patterns or tracts in electronic applications such as printed circuit boards and condensers.

According to another use the polymers according to the present invention, especially their water-soluble derivatives (for example with polar or ionic side groups) or ionically doped forms, can be employed as chemical sensors or materials for detecting and discriminating DNA sequences. Such uses are described for example in L. Chen, D. W. McBranch, H. Wang, R. Helgeson, F. Wudl and D. G. Whitten, Proc. Natl. Acad. Sci. U.S.A. 1999, **96**, 12287; D. Wang, X. Gong, P. S. Heeger, F. Rininsland, G. C. Bazan and A. J. Heeger, Proc. Natl. Acad. Sci. U.S.A. 2002, **99**, 49; N. DiCesare, M. R. Pinot, K. S. Schanze and J. R. Lakowicz, Langmuir 2002, **18**, 7785; D. T. McQuade, A. E. Pullen, T. M. Swager, Chem. Rev. 2000, **100**, 2537.

PCT/EP2006/000360

In the foregoing and the following, all temperatures are given in degrees Celsius, and all percentages are by weight, unless stated otherwise. "Room temperature" means 18 - 20°C.

- 35 -

The examples below serve to illustrate the invention without limiting it. Therein, ¹H- and ¹³C-NMR spectra are recorded on a Bruker AV-300 (300 MHz), using the residual solvent resonance of CDCl₃ as an internal reference and are given in ppm. Mass spectra are obtained from an Agilent GCMS using a 6890 series GC with a 5973 MSD (EI). Molecular weight determinations are carried out in chlorobenzene solution on an Agilent 1100 series HPLC using two Polymer Laboratories mixed B columns in series, and the system is calibrated against narrow weight PL polystyrene calibration standards.

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Example 1

WO 2006/084545

To a dry 3-necked flask under nitrogen is added magnesium filings (354 mg, 14.6 mmol). A solution of 2,5-dibromo-3-hexylthiophene (4.41 g, 13.5 mmol) in anhydrous THF (45 ml) is prepared and 5 ml of this solution is added to the magnesium at 5°C. The reaction is initated by the addition of 2-bromopropane (80 mg, 0.65 mmol). After 5 min, the remaining solution of 2,5-dibromothiophene is added dropwise, keeping the temperature below 10°C. The resulting yellow solution is warmed to room temperature and stirred for 4 h at that temperature. An aliquot is taken, hydrolysed with dilute hydrochloric acid and analysed by GCMS to reveal 98% formation of monogrignard reagent and 2% formation of a digrignard reagent. No starting material remained. The solution is transferred, via cannula, to a new reaction vessel and heated to reflux. 1,2-bis{diphenylphosphinopropane)dichloronickel (II) (72 mg, 1 mol %) is added as a solid and the reaction refluxed for 4 h. The reaction is cooled to room temperature and precipitated into methanol. The resulting polymer is filtered, and washed with additional methanol (soxhlet) and heptane (soxhlet). The resulting polymer is dissolved in chloroform and precipitated into methanol to afford 0.6 g of polymer.

WO 2006/084545 PCT/EP2006/000360

- 36 -

GPC (chlorobenzene): Mn = 10,000; Mw = 15,000.

¹H-NMR affords a regioregularity of 96%.

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Example 2

The reaction is repeated as above using 0.5% of bis{diphenylphosphinopropane)dichloronickel (II) to afford 0.86 g of polymer.

GPC (chlorobenzene): Mn = 12,000; Mw = 22,000.

¹H-NMR affords a regioregularity of 95%.

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WO 2006/084545 PCT/EP2006/000360

Patent Claims

- 1. Process of preparing a polymer from an optionally substituted thiophene having at least two groups that are capable of reacting with magnesium, by reacting said thiophene with magnesium in the presence of a catalytic amount of an organohalide or organomagnesium halide to form a regiochemical Grignard intermediate or a mixture of regiochemical Grignard intermediates, and polymerising said Grignard intermediate(s) in the presence of a suitable catalyst.
 - 2. Process of preparing a regioregular poly(3-substituted thiophene) with a regioregularity of ≥ 95 % head-to-tail (HT) couplings by reacting a 3-substituted thiophene, having chloro and/or bromo groups in 2- and 5-position, with magnesium in the presence of a catalytic amount of an organohalide or organomagnesium halide in a solvent, or a mixture of solvents, to form a regiochemical Grignard intermediate, or a mixture of regiochemical Grignard intermediates, and polymerising said Grignard intermediate in the presence of a suitable catalyst.
 - 3. Process according to claim 1 or 2, by
 - a) providing a suspension of magnesium in an organic solvent,
 - b) adding the thiophene having two groups that are capable of reacting with magnesium, optionally dissolved in a solvent or a mixture of solvents,
 - c) adding the organohalide or organomagnesium halide in an amount from > 0 to 0.5 equivalents of the thiophene, so that the thiophene reacts with the magnesium to form a regiochemical Grignard intermediate or a mixture of regiochemical Grignard intermediates, and optionally adding further of the thiophene or thiophene solution,

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- d) adding the catalyst, or adding the reaction mixture to the catalyst, and optionally agitating the resulting mixture, to form a polymer, and
- e) recovering the polymer from the mixture,

 wherein optionally steps b) and c) are combined by adding the thiophene and the organohalide or organomagnesium halide together to the magnesium, and
- wherein optionally step c) is carried out before step b) by adding the organohalide or organomagnesium halide to the magnesium before the thiophene.
- 4. Process according to at least one of the preceding claims, characterized in that the 3-substituted thiophene is a 3-substituted 2,5-dibromo-thiophene.

- 5. Process according to at least one of the preceding claims, characterized in that the poly (3-substituted thiophene) has a regioregularity of \geq 98 %.
- 6. Process according to at least one of the preceding claims, characterized in that the solvent is THF.
- 7. Process according to at least one of the preceding claims, characterized in that the amount of the magnesium is from 1.02 to 1.20 times the molar amount of the thiophene educt.
- 8. Process according to at least one of the preceding claims, characterized in that the unreacted magnesium is removed from the reaction mixture before adding the catalyst.
 - 9. Process according to at least one of the preceding claims, characterized in that the catalyst is a Ni(II) catalyst.
- 10. Process according to the preceding claim, characterized in that the catalyst is selected from Ni(dppp)Cl₂ (1,3-

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diphenylphosphinopropane nickel(II) chloride) or Ni(dppe)Cl₂ (1,2-bis(diphenylphosphino) ethane nickel(II) chloride).

- 11. Process according to at least one of the preceding claims, characterized in that the formation of the regiochemical
 Grignard intermediate is carried out at a temperature from +5 to -5°C.
- 12. Process according to at least one of the preceding claims,
 10 characterized in that the polymerisation is carried out at a temperature from room temperature to reflux temperature.
 - 13. Process according to at least one of the preceding claims, characterized in that the polymer is purified after being recovered from the reaction mixture.
 - 14. Process according to at least one of the preceding claims, characterized in that the polymer is of formula I

- wherein n is an integer > 1 and R¹ is a group that does not react with magnesium under the conditions of the process according to any of the preceding or following claims.
- 15. Process according to at least one of the preceding claims, 30 characterized in that the 3-substituted thiophene is of formula II

$$X^1$$
 X^2

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wherein R^1 has the meaning of claim 14, and X^1 and X^2 are independently of each other Br or Cl.

- 16. Process according to claim 14 or 15, characterized in that R¹ is selected from C₁-C₂₀-alkyl that is optionally substituted with one or more fluorine atoms, C₁-C₂₀-alkenyl, C₁-C₂₀-alkynyl, C₁-C₂₀-alkoxy, C₁-C₂₀-thioalkyl, C₁-C₂₀-silyl, C₁-C₂₀-amino, C₁-C₂₀-fluoroalkyl.
- 17. Process according to claim 16, characterized in that R¹ is selected from straight-chain or branched pentyl, hexyl, heptyl, octyl, nonyl, decyl, undecyl or dodecyl.
 - 18. Process according to at least one of claims 14 to 17, characterized in that X¹ and X² are Br.
 - 19. Process according to at least one of claims 14 to 18, characterized in that n is an integer from 50 to 1,000.
- 20. Process according to at least one of the preceding claims, characterized in that the polymer is of formula I1

wherein n, R^1 , X^1 and X^2 have the meanings of the preceding claims.

- 21. Process according to at least one of the preceding claims, characterized in that the organohalide or organomagnesium halide is of formula III
- R^3 -(Mg)- X^3 III

wherein

- R^3 is aryl or heteroaryl which is optionally substituted by one or more groups L, or straight chain, 5 branched or cyclic alkyl with 1 to 20 C-atoms, which is optionally mono- or polysubstituted by F, Cl, Br or I, and wherein one or more non-adjacent CH₂ groups are optionally replaced, in each case independently from one another, by -O-, -S-, -NR⁰-, -SiR⁰R⁰⁰-, -CY¹=CY²- or -C≡C- in such a manner 10 that O and/or S atoms are not linked directly to one another, is F, Cl, Br, I, or alkyl, alkoxy or thioalkyl with 1 to L 15 20 C atoms, wherein one or more H atoms may be substituted by F or CI, Y^1 and Y^2 are independently of each other H, F or CI, R⁰ and R⁰⁰ are independently of each other H, alkyl with 1 to 12 20 C-atoms or aryl, Χ is Br, Cl or I, preferably Br.
 - 22. Process according to the preceding claim, characterized in that R³ is straight-chain or branched alkyl or alkenyl with 1 to 12 C atoms, phenyl or benzyl, and X³ is CI or Br.
- 30 23. Process according to at least one of the preceding claims, characterized in that one or more of the terminal groups of the polymer are chemically modified ('endcapped').
- 24. Process according to preceding claim, characterized in that thepolymer after endcapping is of formula I2

$$X^{11}$$
 X^{22} X^{22}

wherein n and R¹ have the meanings of the preceding claims,

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X¹¹ and X²² are independently of each other H, halogen, Sn(R⁰)₃ or straight chain, branched or cyclic alkyl with 1 to 20 C-atoms, which may be unsubstituted, mono- or poly-substituted by F, Cl, Br, I, -CN and/ or -OH, it being also possible for one or more non-adjacent CH₂ groups to be replaced, in each case independently from one another, by -O-, -S-, -NH-, -

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NR⁰-, -SiR⁰R⁰⁰-, -CO-, -COO-, -OCO-, -OCO-O-, -S-CO-, -CO-S-, -CY¹=CY²- or -C≡C- in such a manner that O and/or S atoms are not linked directly to one another, optionally substituted aryl or heteroaryl, or P-Sp,

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R⁰ and R⁰⁰ are independently of each other H or alkyl with 1 to 12 C-atoms, and

Y¹ and Y²

Y² are independently of each other H, F, Cl or CN.

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- 25. Process according to the preceding claim, characterized in that X¹¹ and X²² are independently of each other alkyl that is optionally substituted with one or more fluorine atoms, alkenyl, alkynyl, alkoxy, thioalkyl, silyl, ester, amino or fluoroalkyl, all of these groups being straight-chain or branched and having 1 to 20 C atoms, or optionally substituted aryl or heteroaryl, or P-Sp as defined in claim 19.
- 26. Process according to claim 25, characterized in that X¹¹ and X²² denote straight-chain or branched alkyl with 1 to 6 C atoms.

- 27. Process according to claim 25, characterized in that one or both of X¹¹ and X²² denote a reactive group or a protected reactive group.
- 5 28. Process according to claim 27, characterized in that the polymer of formula I2 is further reacted via end group X¹¹ and/or X²² with the same or a different polymer of formula I2, or with another polymer, to form a block copolymer.
- 10 29. Polymer or copolymer obtained by a process according to at least one of the preceding claims.
- 30. Use of a polymer according to claim 29 as charge-transport, semiconducting, electrically conducting, photoconducting or light-15 emitting material in optical, electrooptical or electronic components or devices, organic field effect transistors (OFET), integrated circuitry (IC), thin film transistors (TFT), flat panel displays, radio frequency identification (RFID) tags, electroluminescent or photoluminescent devices or components, 20 organic light emitting diodes (OLED), backlights of displays, photovoltaic or sensor devices, charge injection layers, Schottky diodes, planarising layers, antistatic films, conducting substrates or patterns, electrode materials in batteries, photoconductors, electrophotographic applications, electrophotographic recording, 25 organic memory devices, alignment layers, or for detecting and discriminating DNA sequences.
 - 31. Semiconductor or charge transport material, component or device comprising one or more polymers according to claim 29.
 - 32. Optical, electrooptical or electronic device, FET, integrated circuit (IC), TFT, OLED or alignment layer comprising a polymer, material, component or device according to claim 29 or 31.

WO 2006/084545 PCT/EP2006/000360

- 44 -

33. TFT or TFT array for flat panel displays, radio frequency identification (RFID) tag, electroluminescent display or backlight, comprising a polymer, material, component or device, FET, IC, TFT or OLED according to claim 29, 31 or 32.

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34. Security marking or device comprising a FET or an RFID tag according to claim 33.

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35. Polymer according to claim 29 which is oxidatively or reductively doped to form conducting ionic species.

36. Charge injection layer, planarising layer, antistatic film or conducting substrate or pattern for electronic applications or flat panel displays, comprising a polymer according to claim 35.

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INTERNATIONAL SEARCH REPORT

international application No PCT/EP2006/000360

A. CLASSIFICATION OF SUBJECT MATTER INV. C08G61/12 H01L51/30

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

 $\begin{array}{ll} \mbox{Minimum documentation searched (classification system followed by classification symbols)} \\ \mbox{C08G} & \mbox{H01L} & \mbox{H01B} \end{array}$

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, WPI Data, CHEM ABS Data

C. DOCUME	ENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of t	he relevant passages	Relevant to claim No.
Х	US 5 247 062 A (SAWADA ET AL) 21 September 1993 (1993-09-21) abstract		1,2,4-7, 9,11-22, 25,27-29
	column 1, line 28 - column 3, claims 1,2; examples 1-5	line 30;	
Х	US 5 391 622 A (HO ET AL) 21 February 1995 (1995-02-21)		1,2,4-7, 9,10, 12-22, 25, 27-30, 33,34
Υ	abstract column 1, line 64 - column 2, claims 1-10; example 1 example 1	line 2;	3,8,23, 24,26
X Furti	ner documents are listed in the continuation of Box C.	_/ X See patent family annex.	
		The patent laminy aimex.	
"A" docume consid "E" earlier of filing d "L" docume which citation "O" docume other r "P" docume	ent which may throw doubts on priority claim(s) or is cited to establish the publication date of another n or other special reason (as specified) ent referring to an oral disclosure, use, exhibition or	 "T" later document published after the inte or priority date and not in conflict with cited to understand the principle or the invention "X" document of particular relevance; the cannot be considered novel or cannot involve an inventive step when the do "Y" document of particular relevance; the cannot be considered to involve an in document is combined with one or moments, such combination being obvious in the art. "&" document member of the same patent 	the application but every underlying the search underlying the standard to cument is taken alone laimed invention wentive step when the ore other such docuus to a person skilled
	actual completion of the international search	Date of mailing of the international sea	rch report
2	4 April 2006	20/06/2006	
Name and r	mailing address of the ISA/ European Patent Office, P.B. 5818 Patentlaan 2 NL - 2280 HV Rijswijk Tel (2017 70) 243 2640 TV 21 651 open!	Authorized officer	
	Tel. (+31-70) 340-2040, Tx. 31 651 epo nl, Fax: (+31-70) 340-3016	Meiners, C	

INTERNATIONAL SEARCH REPORT

International application No
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INTERNATIONAL SEARCH REPORT

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